



New Product

Si4862DY
Vishay Siliconix

N-Channel 16-V (D-S) MOSFET

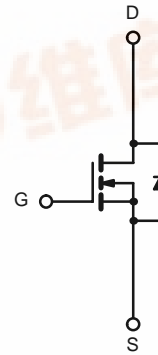
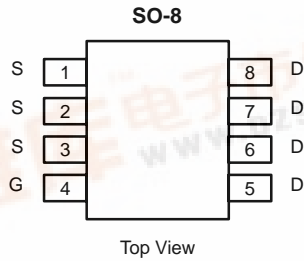
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
16	0.0033 @ $V_{GS} = 4.5$ V	25
	0.0055 @ $V_{GS} = 2.5$ V	20

FEATURES

- TrenchFET® Power MOSFETS: 2.5-V Rated
- Low 3.3-m Ω $r_{DS(on)}$
- Low Gate Resistance
- 100% R_G Tested

APPLICATIONS

- Synchronous Rectification
- Low Output Voltage Synchronous Rectification



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	16		V	
Gate-Source Voltage	V_{GS}	± 8			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	25	17	A
		$T_A = 70^\circ\text{C}$	20	13	
Pulsed Drain Current (10 μs Pulse Width)	I_{DM}	60			
Continuous Source Current (Diode Conduction) ^a	I_S	2.9	1.3		
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	3.5	1.6	W
		$T_A = 70^\circ\text{C}$	2.2	1	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	29	35	$^\circ\text{C/W}$
		Steady State	67	80	
Maximum Junction-to-Foot (Drain)	R_{thJF}	13	16		

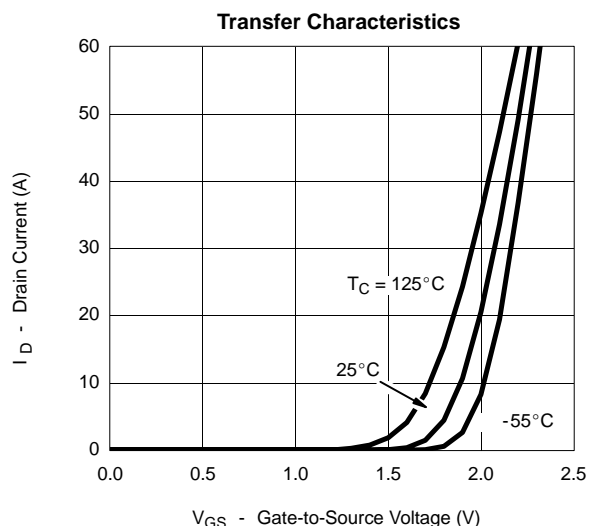
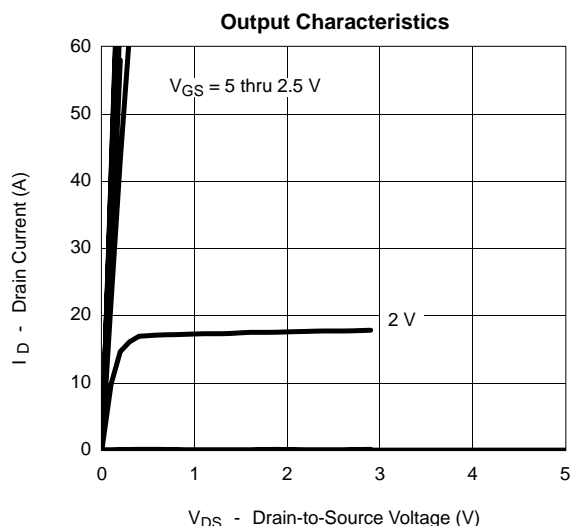
Notes:
a. Surface Mounted on 1" x 1" FR4 Board.


SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.6			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 12.8 V, V _{GS} = 0 V			1	μA
		V _{DS} = 12.8 V, V _{GS} = 0 V, T _J = 55 °C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	30			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 25 A		0.0027	0.0033	Ω
		V _{GS} = 2.5 V, I _D = 20 A		0.0045	0.0055	
Forward Transconductance ^a	g _{fs}	V _{DS} = 6 V, I _D = 25 A		140		S
Diode Forward Voltage ^a	V _{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 6 V, V _{GS} = 4.5 V, I _D = 25 A		48	70	nC
Gate-Source Charge	Q _{gs}			11.8		
Gate-Drain Charge	Q _{gd}			8.9		
Gate Resistance	R _g		0.5	1.3	2.2	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 6 V, R _L = 6 Ω I _D ≅ 1 A, V _{GEN} = 4.5 V, R _G = 6 Ω		42	60	ns
Rise Time	t _r			38	60	
Turn-Off Delay Time	t _{d(off)}			120	180	
Fall Time	t _f			50	75	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, di/dt = 100 A/μs		80	120	

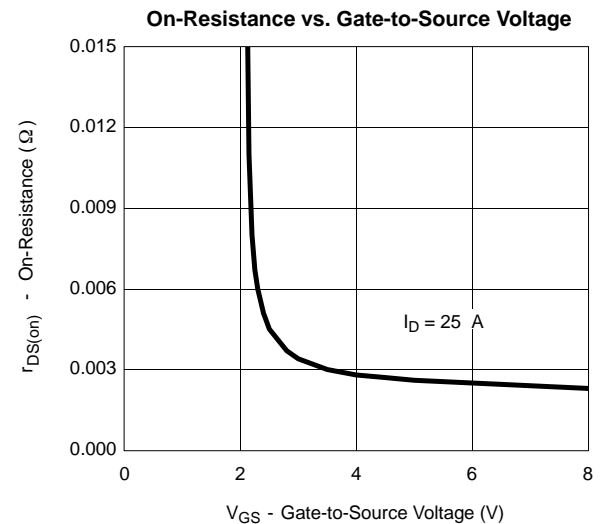
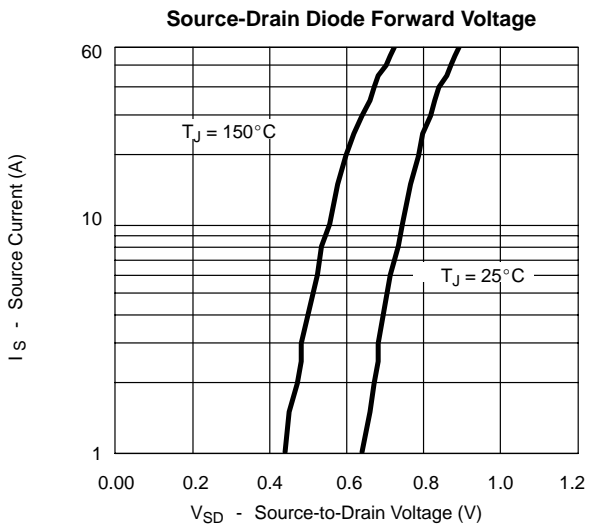
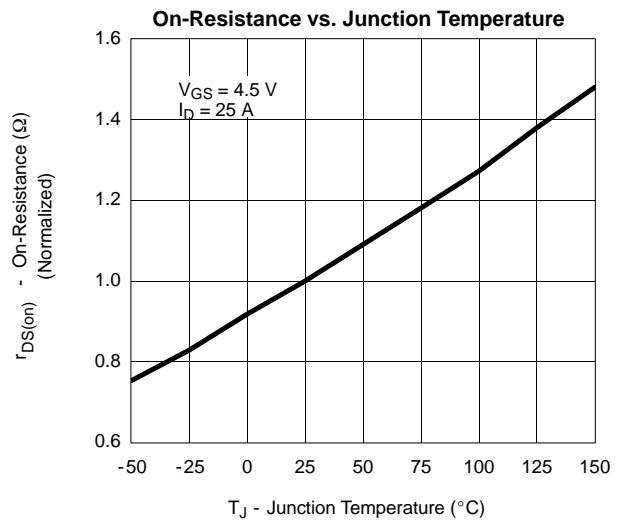
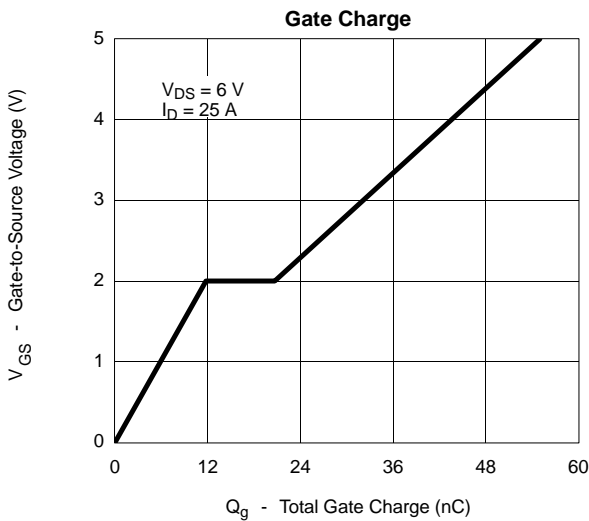
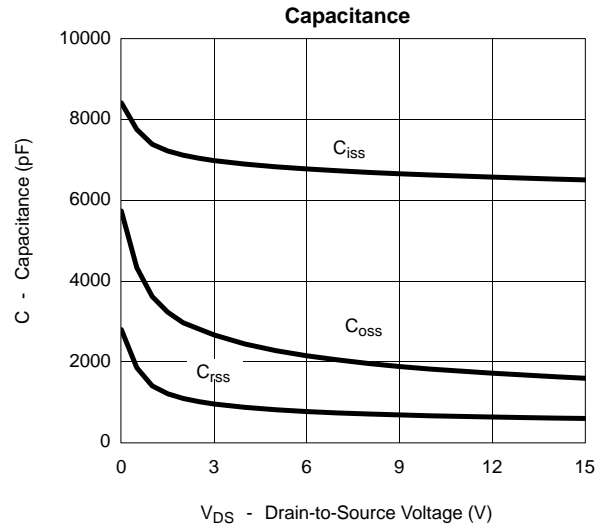
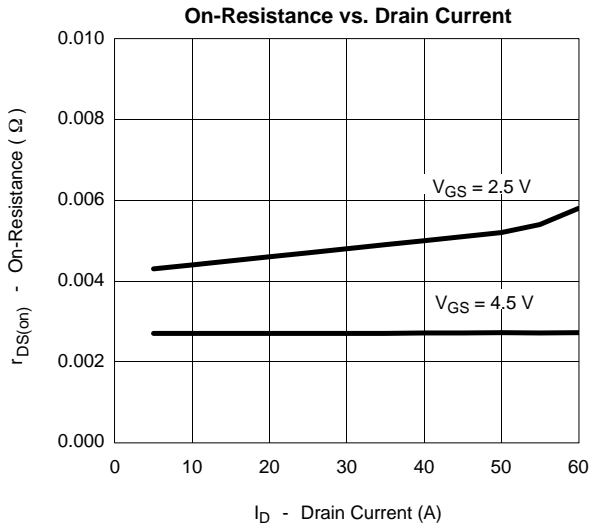
Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)




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